

**40V COMPLEMENTARY NPN/PNP SMALL SIGNAL TRANSISTOR IN SOT963**

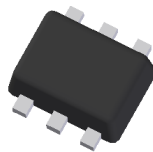
**Features**

- $BV_{CEO} > 40V$
- $I_C = 200mA$  Collector Current
- SOT963 Ultra Small Package of  $1mm^2$  Footprint
- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

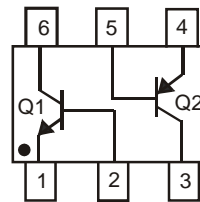
**Mechanical Data**

- Case: SOT963
- Case Material: Molded Plastic "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208(3)
- Weight: 0.0027 grams (Approximate)

SOT963



Top View



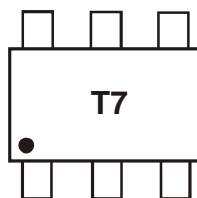
Top View  
Device Schematic  
and Pin-Out

**Ordering Information** (Note 4)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DST3946DPJ-7	T7	7	8	10,000
DST3946DPJ-7B	T7	7	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**



T7 = Product Type Marking Code

**Absolute Maximum Ratings - NPN (Q1)** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CB0</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current	I <sub>C</sub>	200	mA

**Absolute Maximum Ratings - PNP (Q2)** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current	I <sub>C</sub>	-200	mA

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	300	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	417	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Note: 5. Device mounted on FR-4 PCB with minimum recommended pad layout.

**ESD Rating** (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	B

Note: 6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

**Thermal Characteristics and Derating Information**

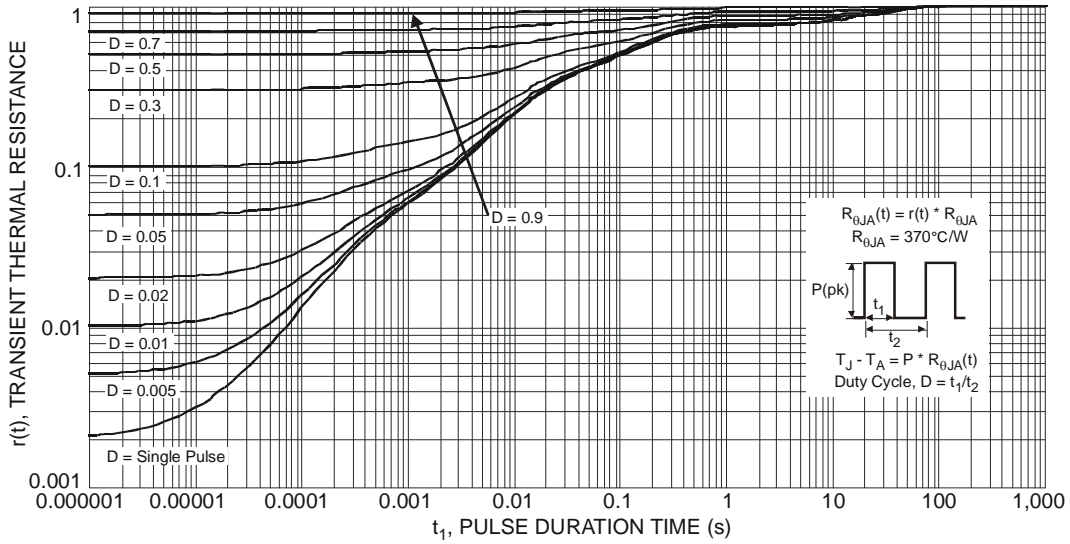


Fig. 1 Transient Thermal Response

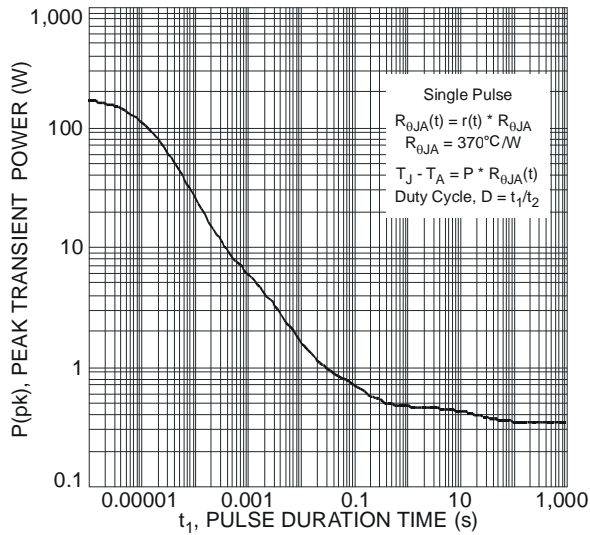


Fig. 2 Single Pulse Maximum Power Dissipation

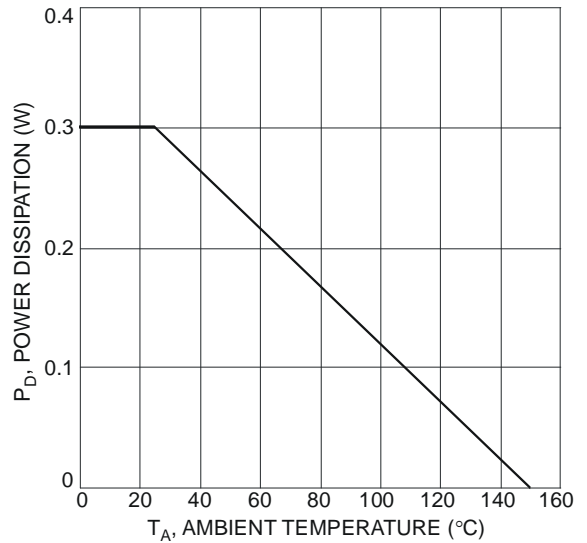


Fig. 3 Power Dissipation vs. Ambient Temperature

**Electrical Characteristics - NPN (Q1)** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60	—	V	I <sub>C</sub> = 10μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage (Note 7)	BV <sub>CEO</sub>	40	—	V	I <sub>C</sub> = 1.0mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6.0	—	V	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0
Collector Cutoff Current	I <sub>CEX</sub>	—	50	nA	V <sub>CE</sub> = 30V, V <sub>EB(OFF)</sub> = 3.0V
Base Cutoff Current	I <sub>BL</sub>	—	50	nA	V <sub>CE</sub> = 30V, V <sub>EB(OFF)</sub> = 3.0V
<b>ON CHARACTERISTICS (Note 7)</b>					
DC Current Gain	h <sub>FE</sub>	40	—	—	I <sub>C</sub> = 100μA, V <sub>CE</sub> = 1.0V
		70	—		I <sub>C</sub> = 1.0mA, V <sub>CE</sub> = 1.0V
		100	300		I <sub>C</sub> = 10mA, V <sub>CE</sub> = 1.0V
		60	—		I <sub>C</sub> = 50mA, V <sub>CE</sub> = 1.0V
		30	—		I <sub>C</sub> = 100mA, V <sub>CE</sub> = 1.0V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	0.20 0.30	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	0.65 —	0.85 0.95	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	C <sub>OBO</sub>	—	4.0	pF	V <sub>CB</sub> = 5.0V, f = 1.0MHz, I <sub>E</sub> = 0
Input Capacitance	C <sub>IBO</sub>	—	8.5	pF	V <sub>EB</sub> = 0.5V, f = 1.0MHz, I <sub>C</sub> = 0
Input Impedance	h <sub>iE</sub>	1.0	10	kΩ	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h <sub>RE</sub>	0.5	8.0	x 10 <sup>-4</sup>	
Small Signal Current Gain	h <sub>FE</sub>	100	400	—	
Output Admittance	h <sub>oE</sub>	1.0	40	μs	
Current Gain-Bandwidth Product	f <sub>T</sub>	300	—	MHz	V <sub>CE</sub> = 20V, I <sub>C</sub> = 10mA, f = 100MHz
<b>SWITCHING CHARACTERISTICS</b>					
Delay Time	t <sub>d</sub>	—	35	ns	V <sub>CC</sub> = 3.0V, I <sub>C</sub> = 10mA, V <sub>BE(OFF)</sub> = -0.5V, I <sub>B1</sub> = 1.0mA
Rise Time	t <sub>r</sub>	—	35	ns	
Storage Time	t <sub>s</sub>	—	200	ns	V <sub>CC</sub> = 3.0V, I <sub>C</sub> = 10mA, I <sub>B1</sub> = -I <sub>B2</sub> = 1.0mA
Fall Time	t <sub>f</sub>	—	50	ns	

Note: 7. Short duration pulse test used to minimize self-heating effect.

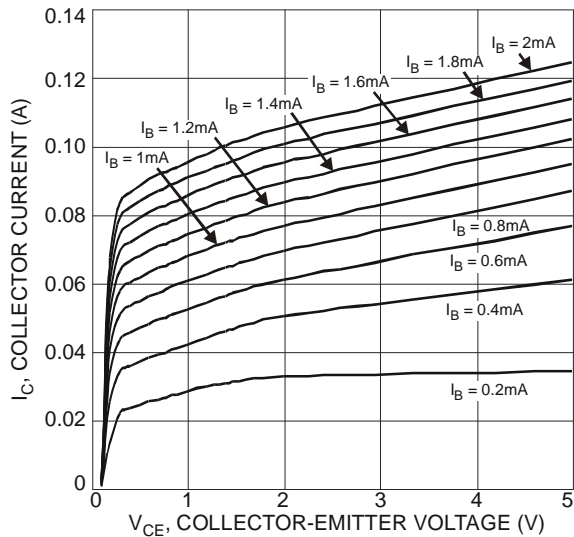


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

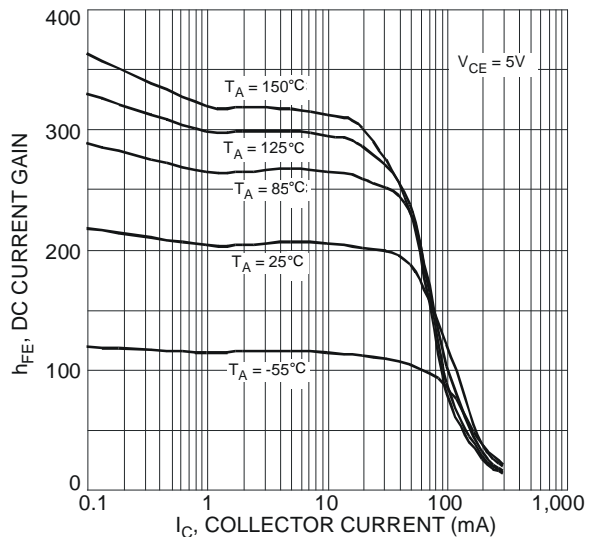


Fig. 5 Typical DC Current Gain vs. Collector Current

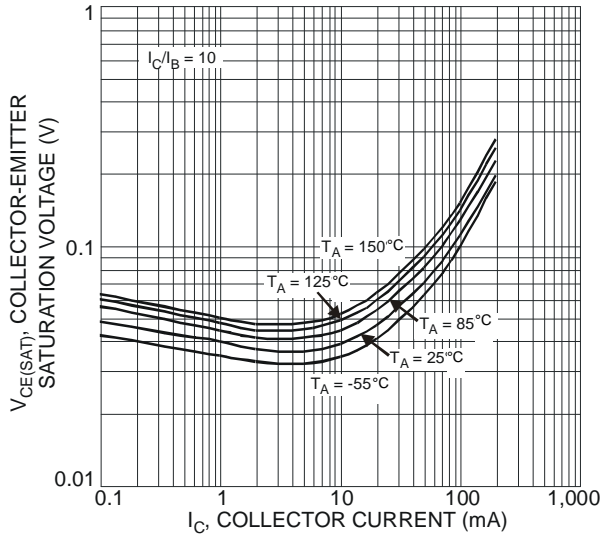


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

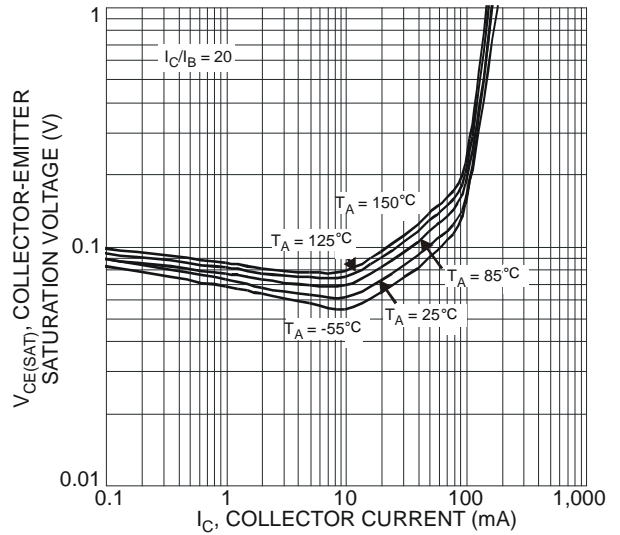


Fig. 7 Typical Collector-Emitter Saturation Voltage vs. Collector Current

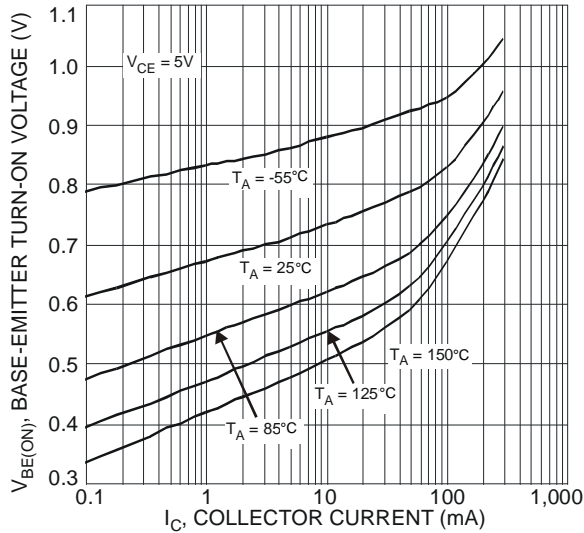


Fig. 8 Typical Base-Emitter Turn-On Voltage vs. Collector Current

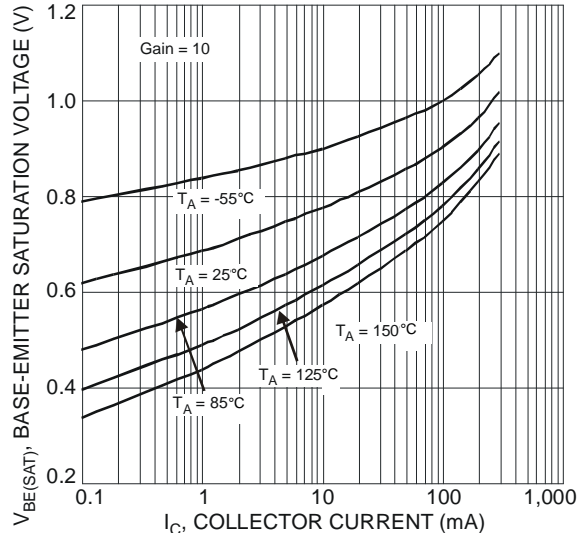


Fig. 9 Typical Base-Emitter Saturation Voltage vs. Collector Current

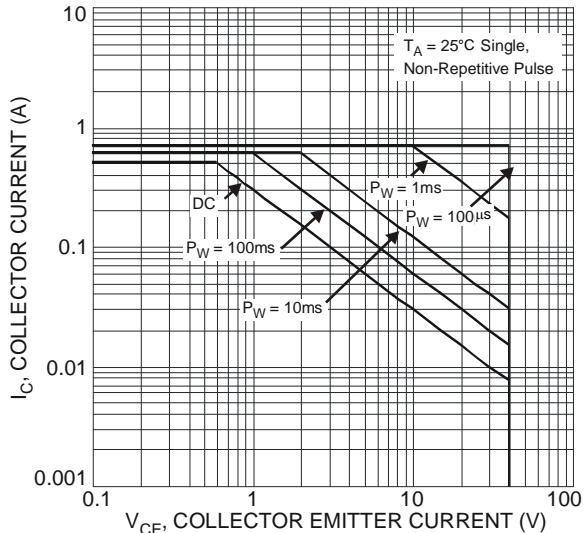


Fig. 10 Safe Operation Area (NPN)

**Electrical Characteristics - PNP (Q2)** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-40	—	V	I <sub>C</sub> = -10μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage (Note 8)	BV <sub>CEO</sub>	-40	—	V	I <sub>C</sub> = -1.0mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5.0	—	V	I <sub>E</sub> = -10μA, I <sub>C</sub> = 0
Collector Cutoff Current	I <sub>CEX</sub>	—	-50	nA	V <sub>CE</sub> = -30V, V <sub>EB(OFF)</sub> = -3.0V
	I <sub>CBO</sub>	—	-50	nA	V <sub>CE</sub> = -30V, I <sub>E</sub> = 0
Base Cutoff Current	I <sub>BL</sub>	—	-50	nA	V <sub>CE</sub> = -30V, V <sub>EB(OFF)</sub> = -3.0V
<b>ON CHARACTERISTICS (Note 8)</b>					
DC Current Gain	h <sub>FE</sub>	60	—	—	I <sub>C</sub> = -100μA, V <sub>CE</sub> = -1.0V
		80	—		I <sub>C</sub> = -1.0mA, V <sub>CE</sub> = -1.0V
		100	300		I <sub>C</sub> = -10mA, V <sub>CE</sub> = -1.0V
		60	—		I <sub>C</sub> = -50mA, V <sub>CE</sub> = -1.0V
		30	—		I <sub>C</sub> = -100mA, V <sub>CE</sub> = -1.0V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	-0.25 -0.40	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	-0.65 —	-0.85 -0.95	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	C <sub>OBO</sub>	—	4.5	pF	V <sub>CB</sub> = -5.0V, f = 1.0MHz, I <sub>E</sub> = 0
Input Capacitance	C <sub>IBO</sub>	—	10	pF	V <sub>EB</sub> = -0.5V, f = 1.0MHz, I <sub>C</sub> = 0
Input Impedance	h <sub>IE</sub>	2.0	12	kΩ	V <sub>CE</sub> = -10V, I <sub>C</sub> = -1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h <sub>RE</sub>	0.1	10	x 10 <sup>-4</sup>	
Small Signal Current Gain	h <sub>FE</sub>	100	400	—	
Output Admittance	h <sub>OE</sub>	3.0	60	μS	
Current Gain-Bandwidth Product	f <sub>T</sub>	300	—	MHz	
<b>SWITCHING CHARACTERISTICS</b>					
Delay Time	t <sub>D</sub>	—	35	ns	V <sub>CC</sub> = -3.0V, I <sub>C</sub> = -10mA, V <sub>BE(OFF)</sub> = 0.5V, I <sub>B1</sub> = -1.0mA
Rise Time	t <sub>R</sub>	—	35	ns	V <sub>CC</sub> = -3.0V, I <sub>C</sub> = -10mA, I <sub>B1</sub> = -I <sub>B2</sub> = -1.0mA
Storage Time	t <sub>S</sub>	—	225	ns	
Fall Time	t <sub>F</sub>	—	75	ns	

Note: 8. Short duration pulse test used to minimize self-heating effect.

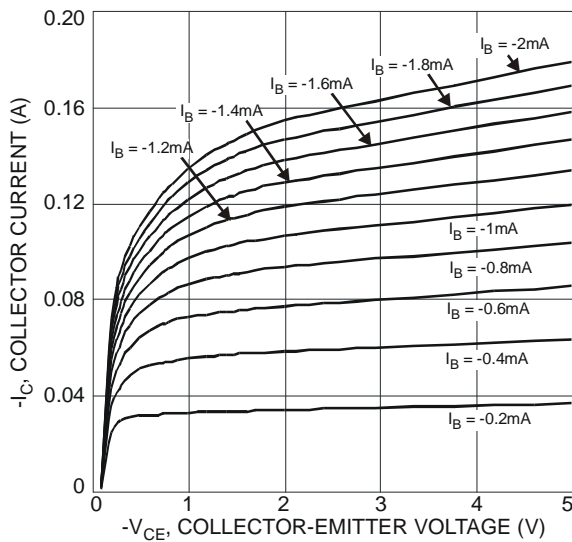


Fig. 11 Typical Collector Current vs. Collector-Emitter Voltage

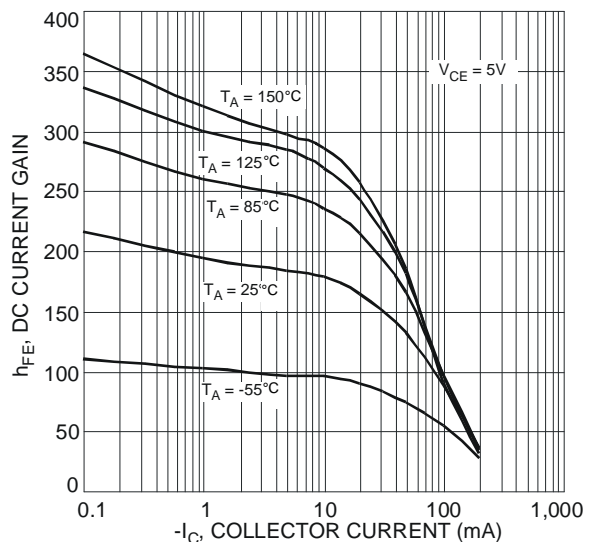


Fig. 12 Typical DC Current Gain vs. Collector Current

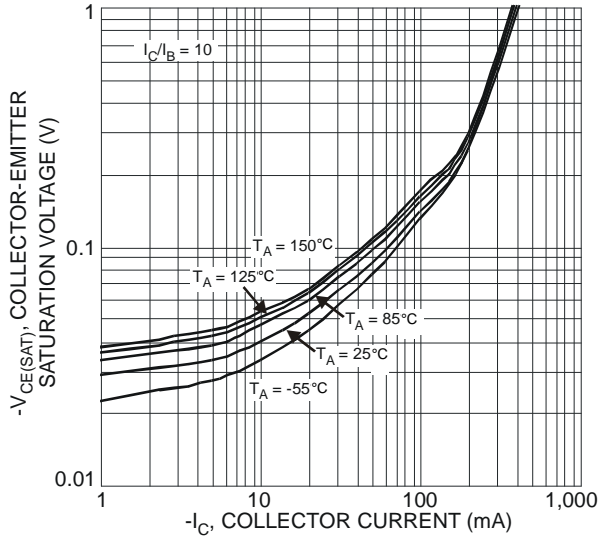


Fig. 13 Typical Collector-Emitter Saturation Voltage vs. Collector Current

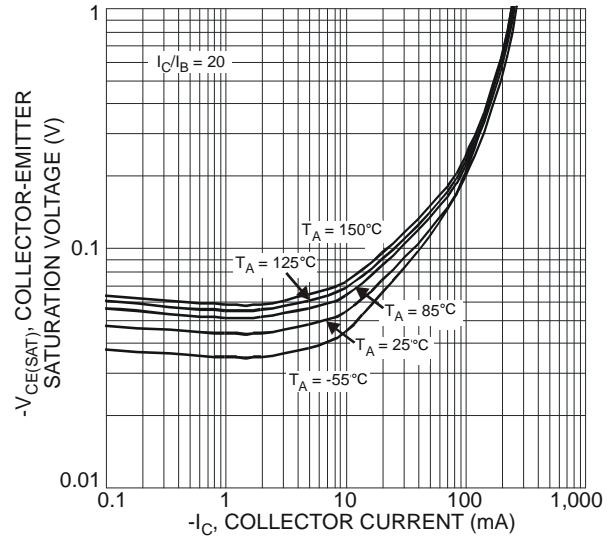


Fig. 14 Typical Collector-Emitter Saturation Voltage vs. Collector Current

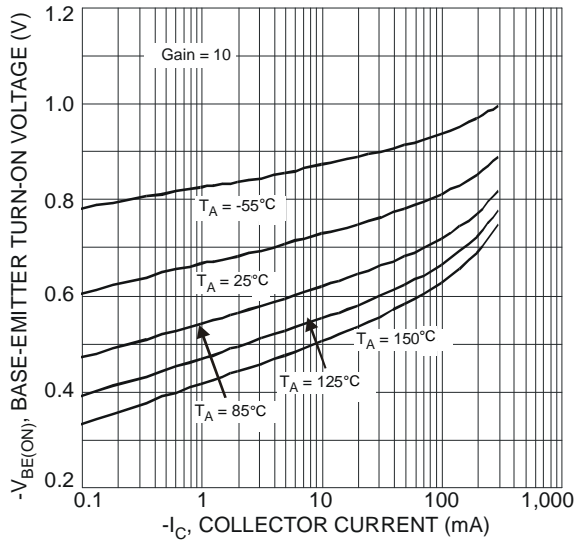


Fig. 15 Typical Base-Emitter Saturation Voltage vs. Collector Current

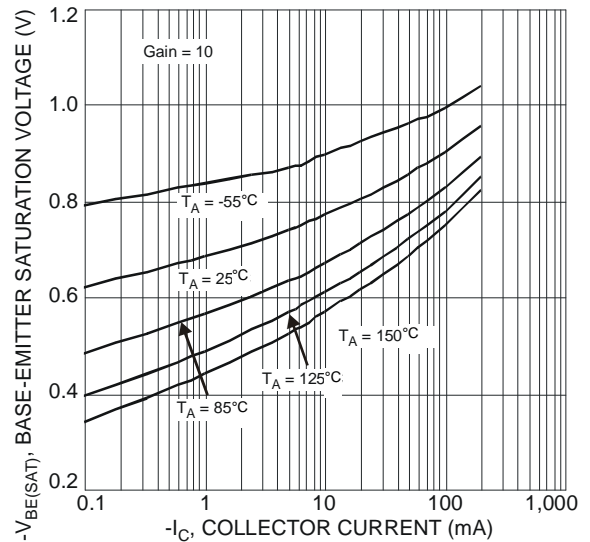


Fig. 16 Typical Base-Emitter Saturation Voltage vs. Collector Current

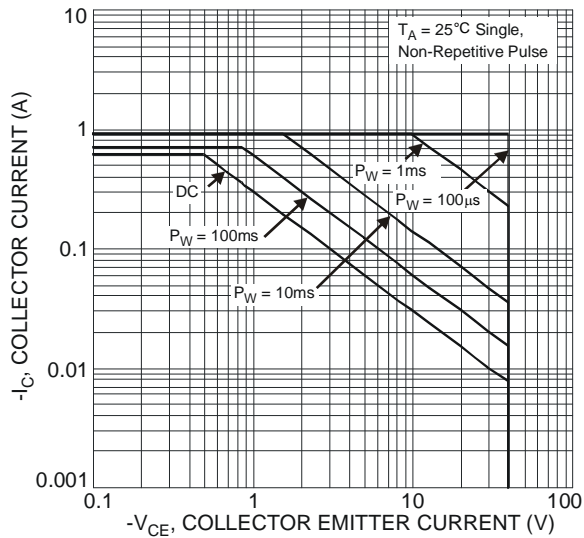
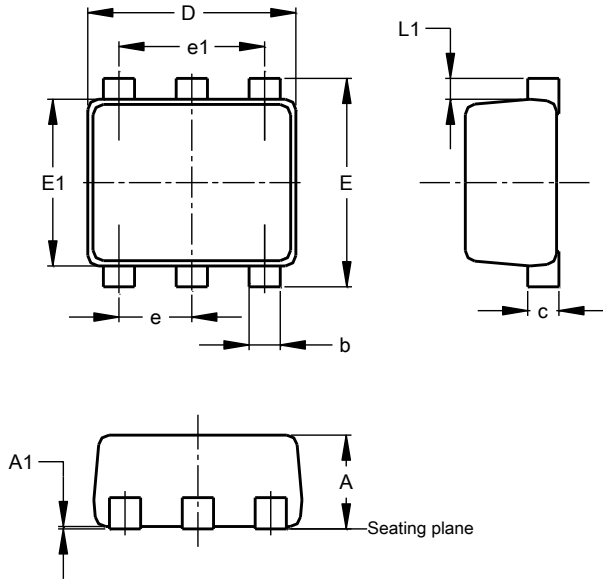


Fig. 17 Safe Operation Area (PNP)

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT963**

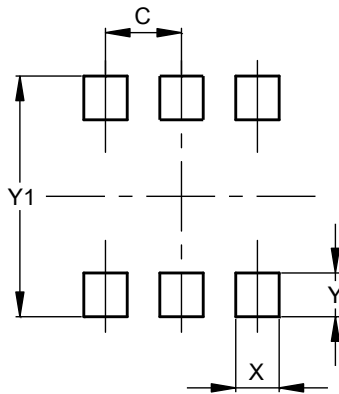


SOT963			
Dim	Min	Max	Typ
A	0.40	0.50	0.45
A1	0.00	0.05	--
b	0.10	0.20	0.15
c	0.120	0.180	0.150
D	0.95	1.05	1.00
E	0.95	1.05	1.00
E1	0.75	0.85	0.80
e	--	--	0.35
e1	--	--	0.70
L1	0.05	0.15	0.10
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT963**



Dimensions	Value (in mm)
C	0.350
X	0.200
Y	0.200
Y1	1.100



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